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(54) **NONVOLATILE SEMICONDUCTOR
MEMORY DEVICE AND METHOD FOR
MANUFACTURING SAME**

(71) Applicant: **Kabushiki Kaisha Toshiba**, Minato-ku
(JP)

(72) Inventor: **Fumiki Aiso**, Mie-ken (JP)

(73) Assignee: **Kabushiki Kaisha Toshiba**, Minato-ku
(JP)

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4, 2013.

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H01L 27/115 (2006.01)

H01L 29/423 (2006.01)

H01L 29/66 (2006.01)

(52) **U.S. Cl.**

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(2013.01); **H01L 29/42328** (2013.01); **H01L**
29/66825 (2013.01); **H01L 29/7881** (2013.01)

(58) **Field of Classification Search**

CPC H01L 29/42328

USPC 257/320, 757

See application file for complete search history.

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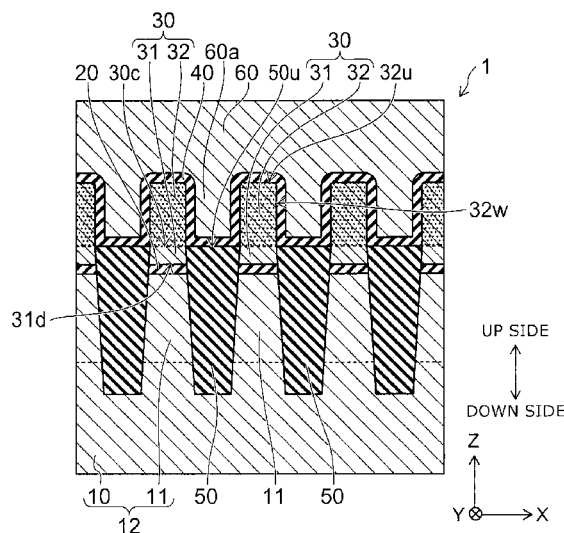
Primary Examiner — Chandra Chaudhari

(74) *Attorney, Agent, or Firm* — Oblon, McClelland, Maier
& Neustadt, L.L.P.

(57) **ABSTRACT**

According to one embodiment, a nonvolatile semiconductor memory device includes: a plurality of first semiconductor regions; a plurality of control gate electrodes; a charge storage layer; a first insulating film provided between the charge storage layer and first semiconductor regions; a second insulating film provided between the charge storage layer and control gate electrodes; and an element isolation region provided between the plurality of first semiconductor regions, and the element isolation region being in contact with the first insulating film and a first portion of the charge storage layer on the first insulating film side. Each of the plurality of control gate electrodes is in contact with a second portion other than the first portion of the charge storage layer. The charge storage layer includes a silicon-containing layer in contact with the first insulating film and a silicide-containing layer provided on the silicon-containing layer.

6 Claims, 17 Drawing Sheets



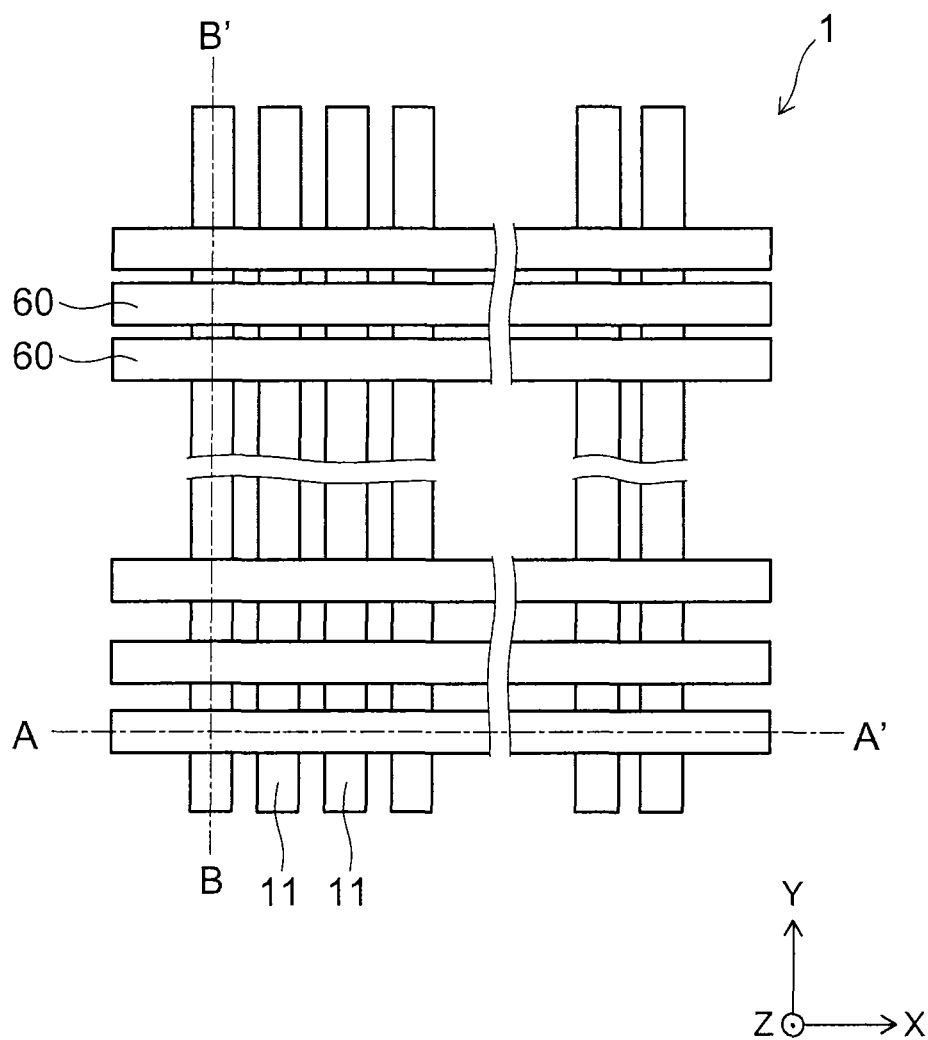


FIG. 1

FIG. 2A

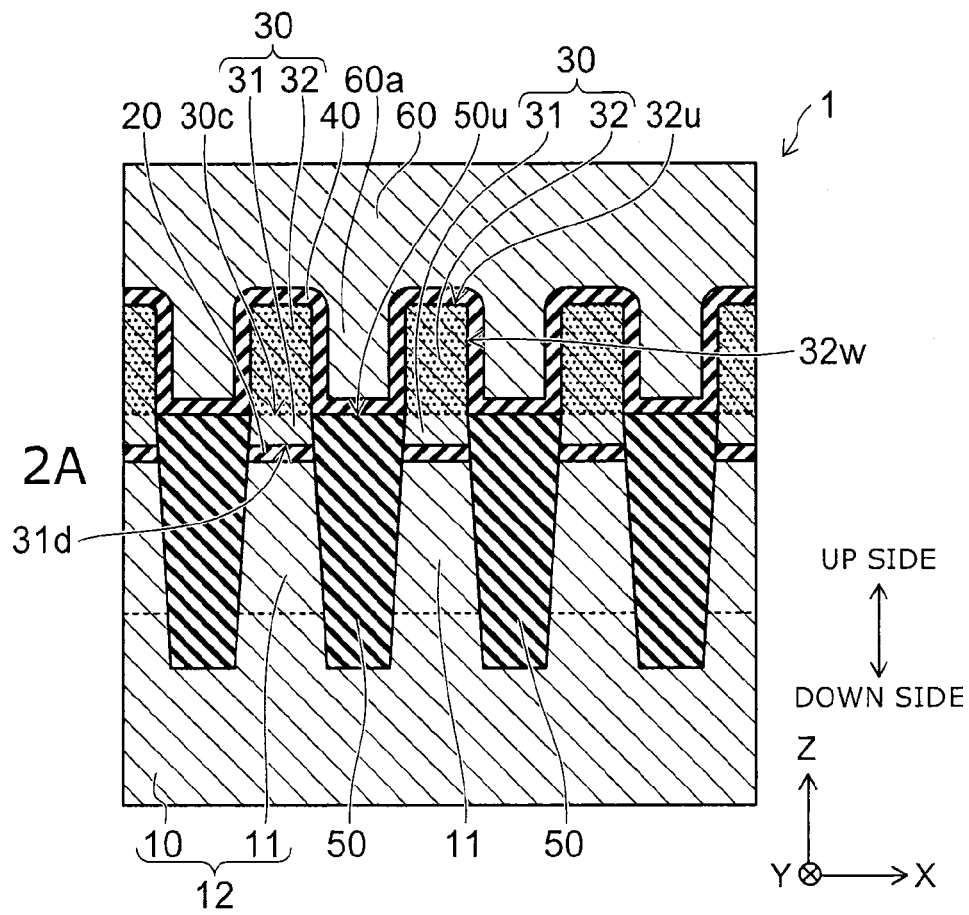
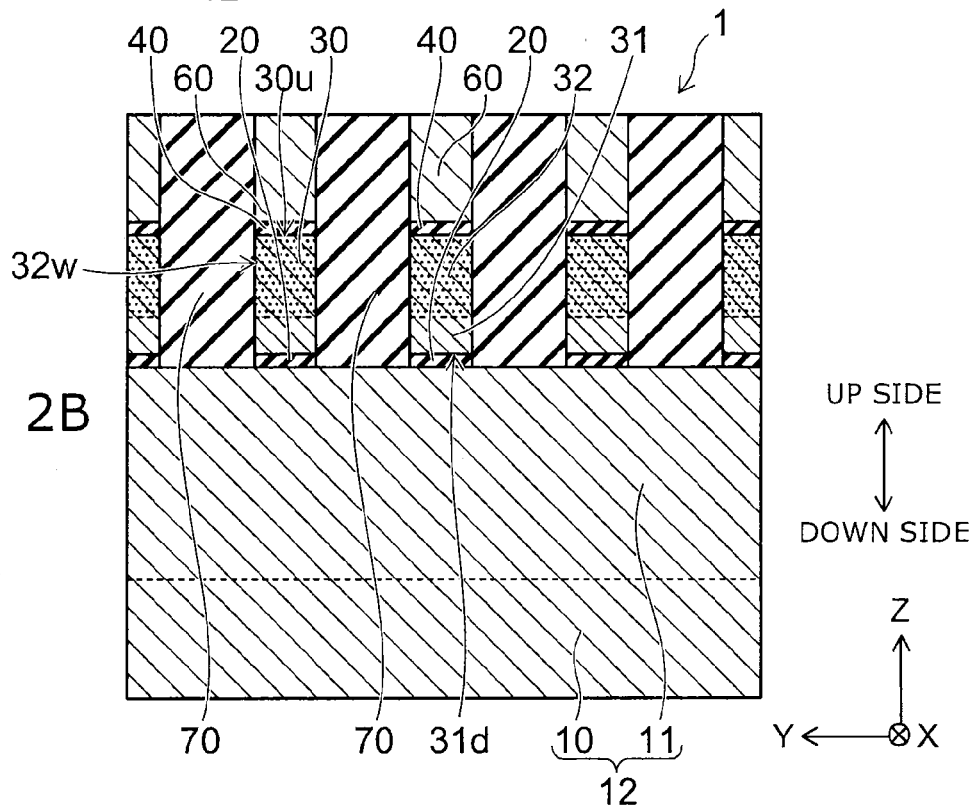


FIG. 2B



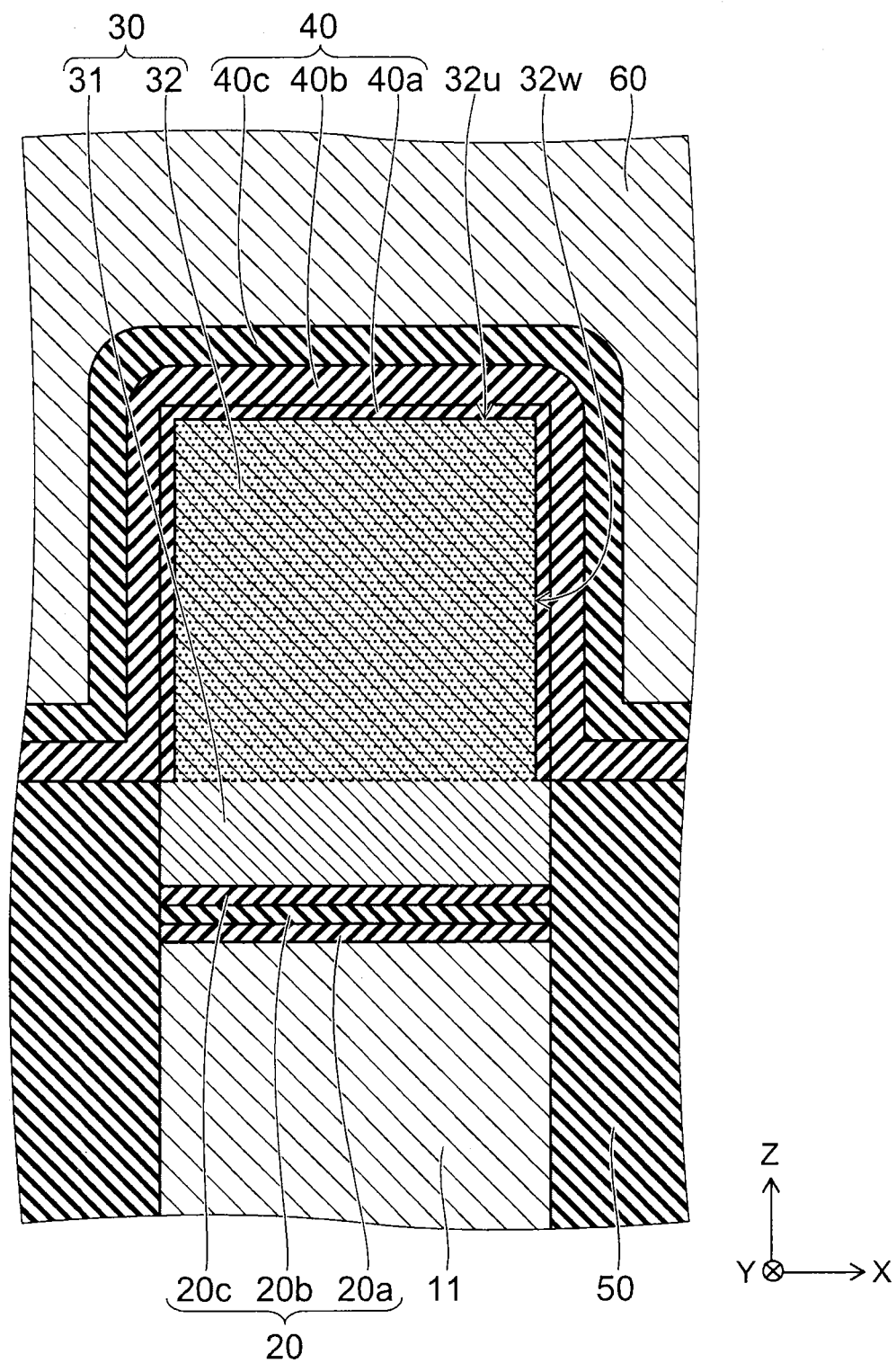


FIG. 3

FIG. 4A

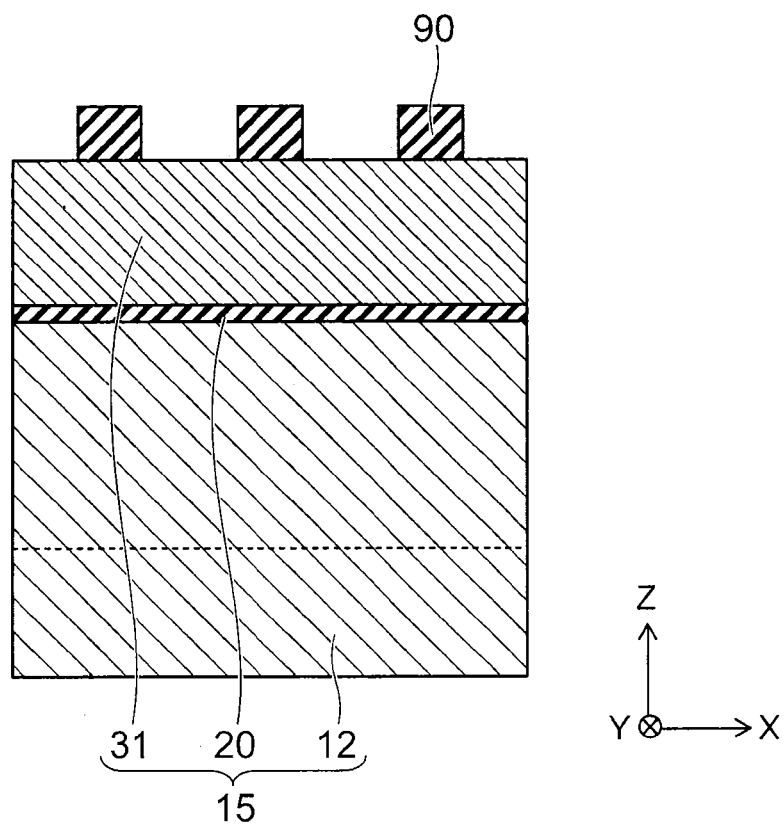


FIG. 4B

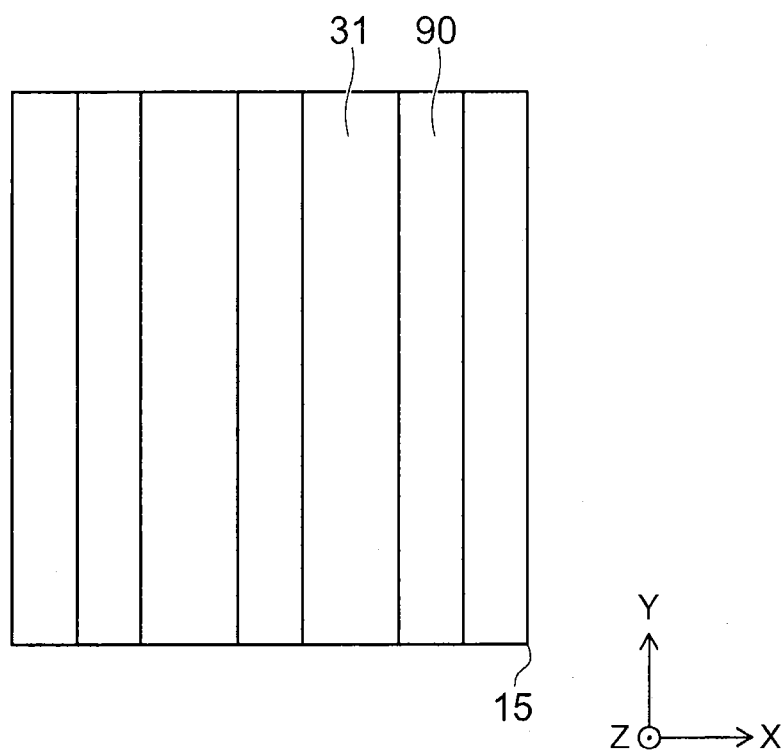


FIG. 5A

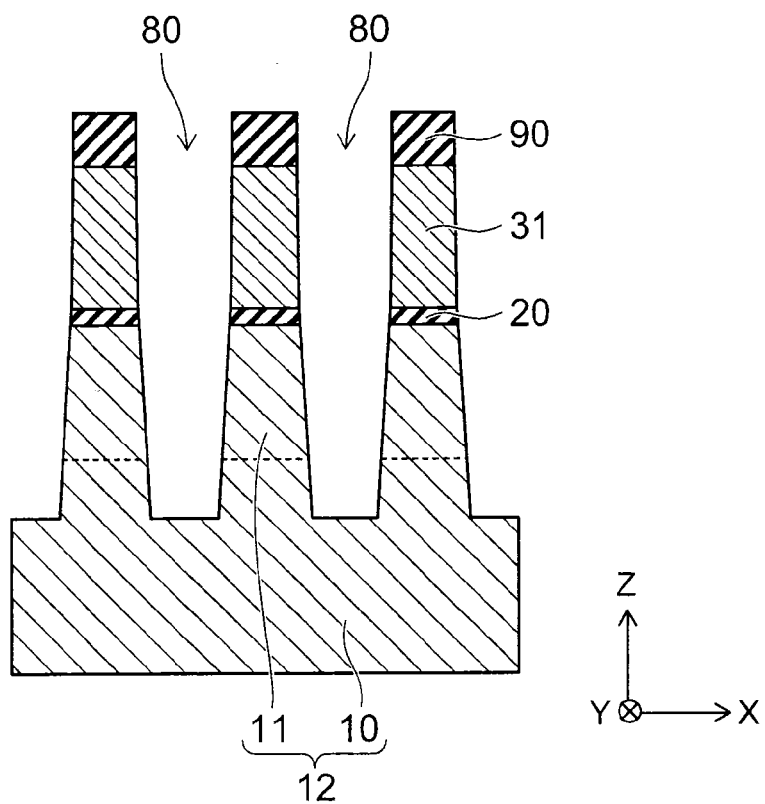


FIG. 5B

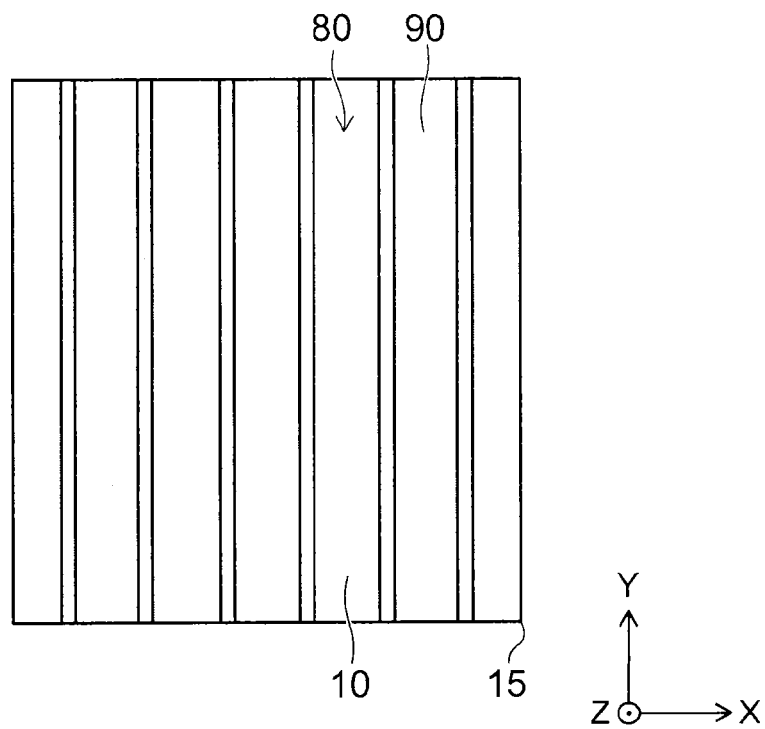


FIG. 6A

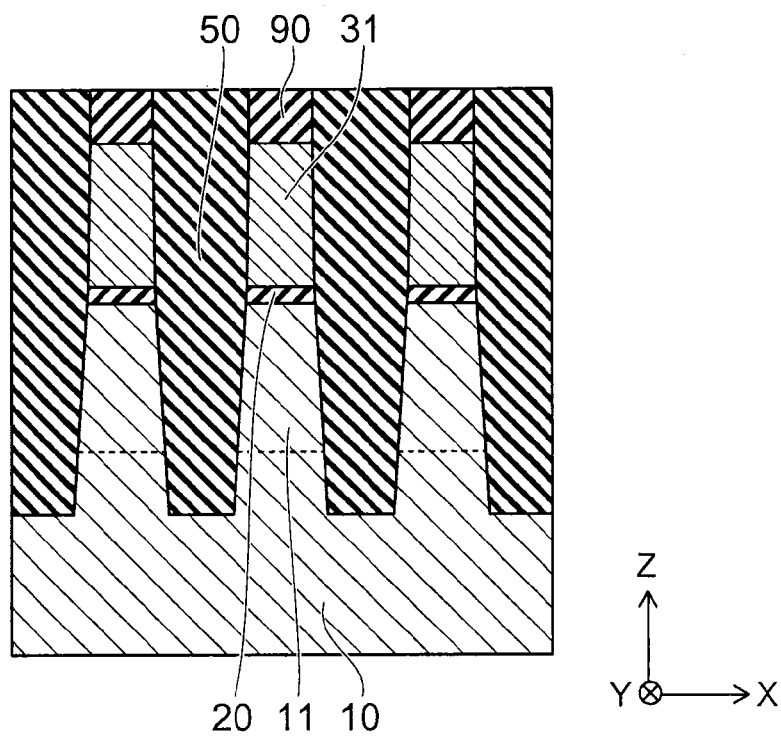


FIG. 6B

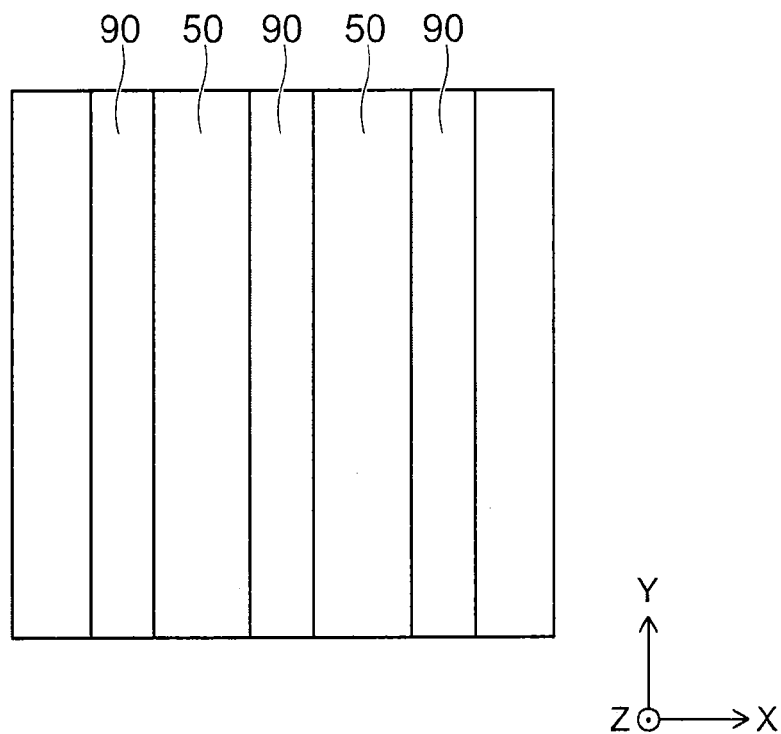


FIG. 7A

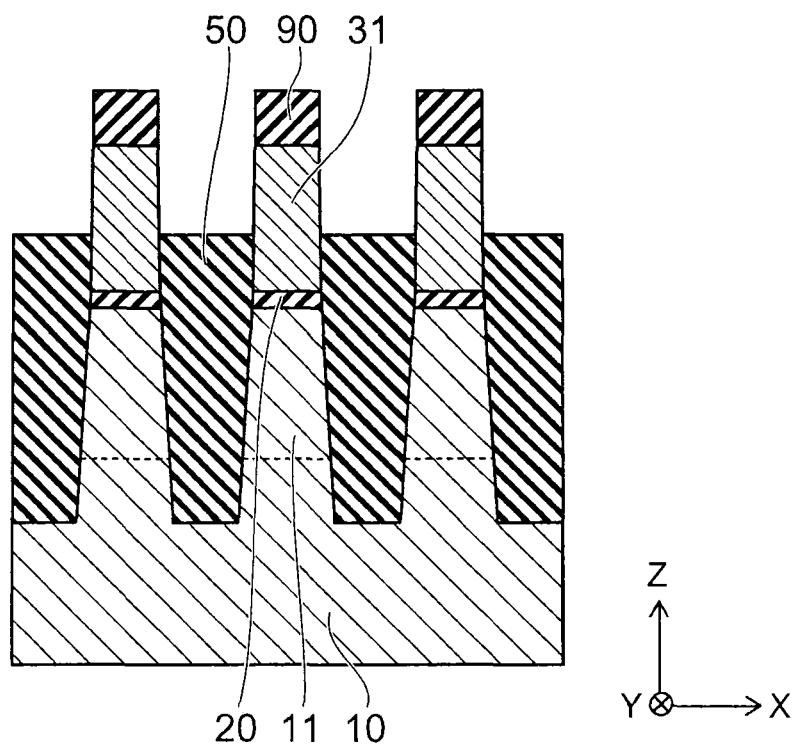


FIG. 7B

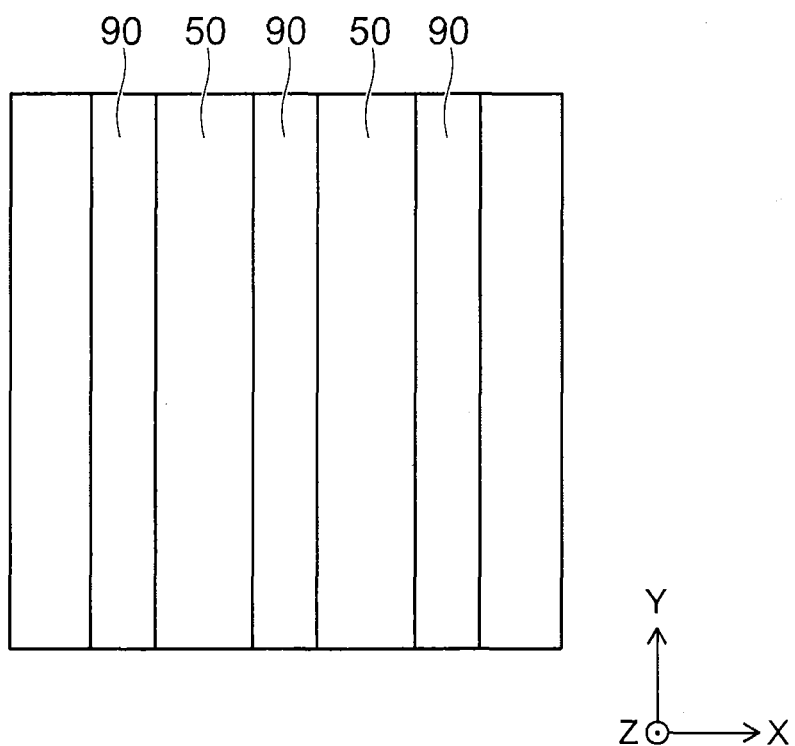


FIG. 8A

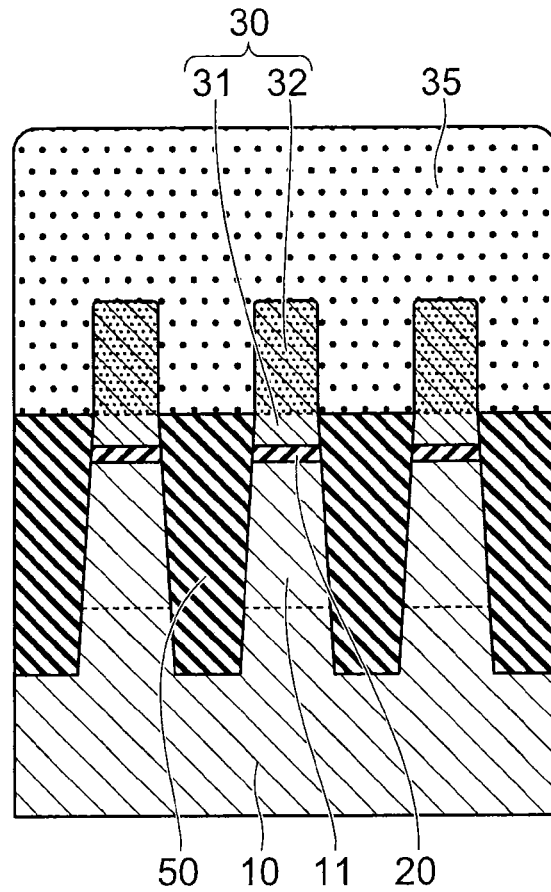


FIG. 8B

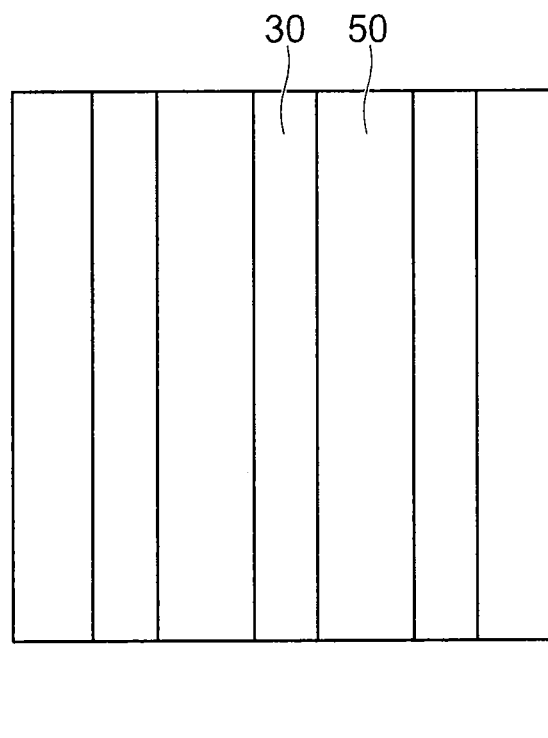


FIG. 9A

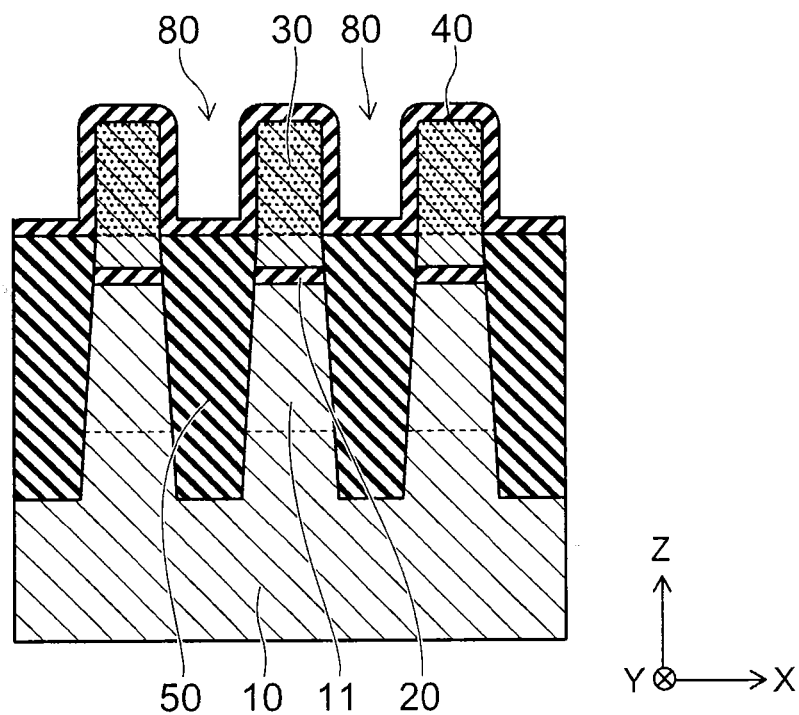


FIG. 9B

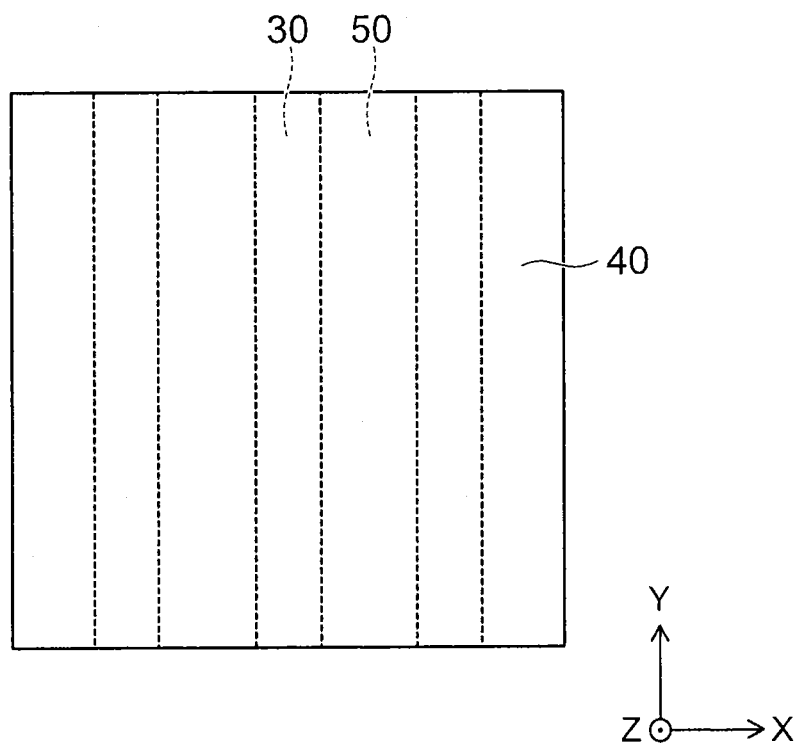


FIG. 10A

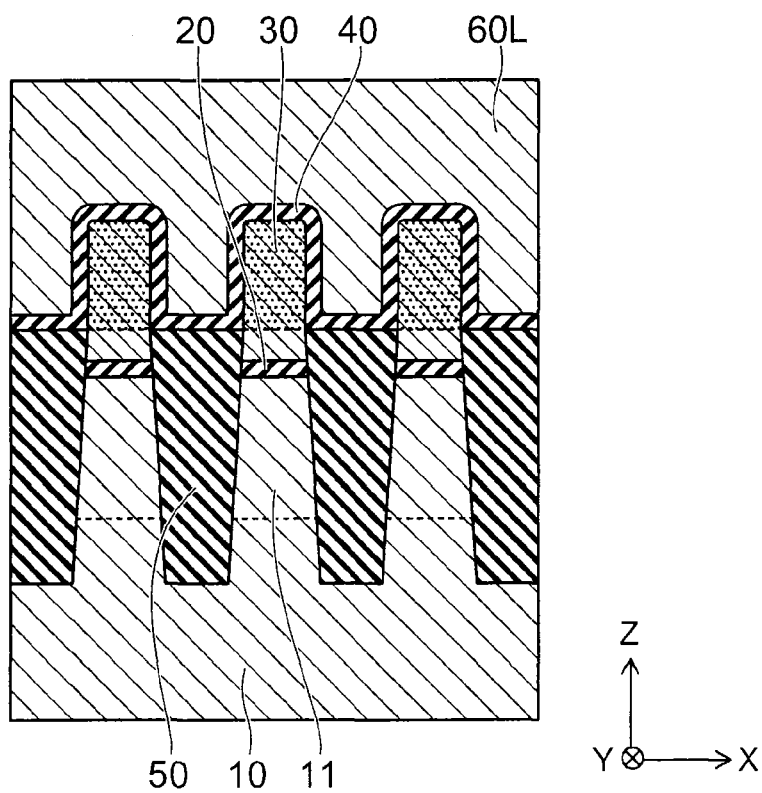


FIG. 10B

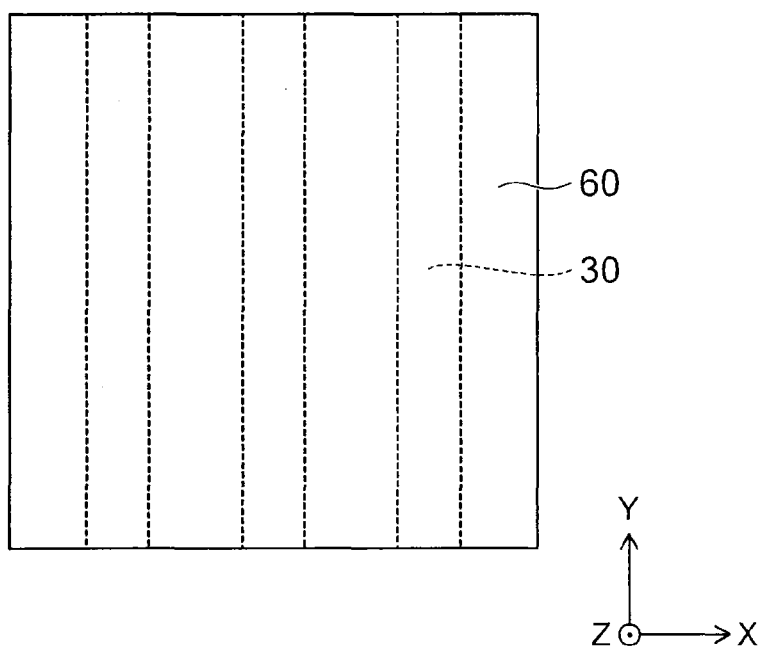


FIG. 11A

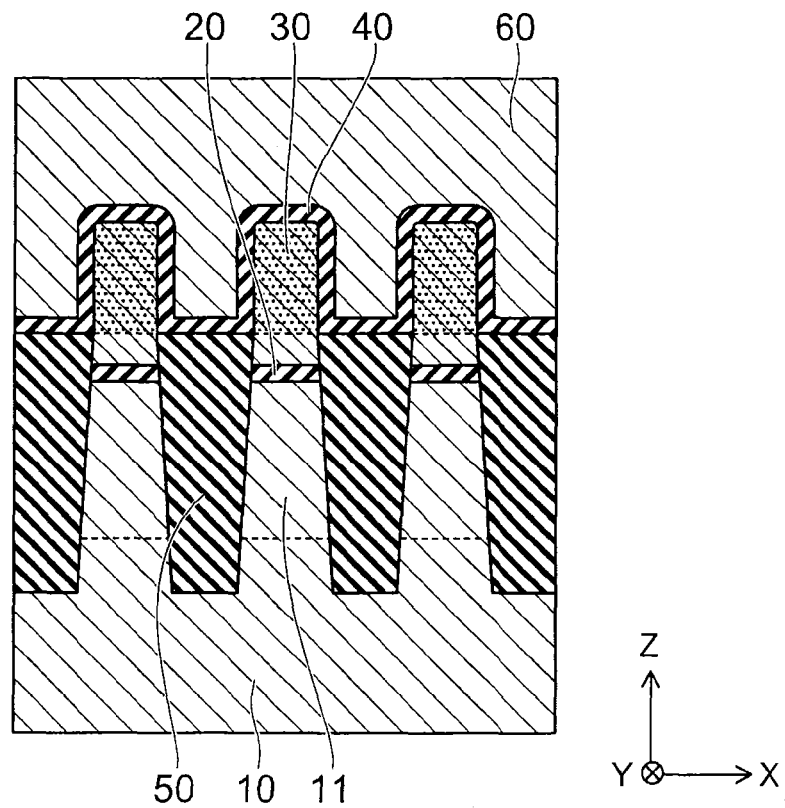
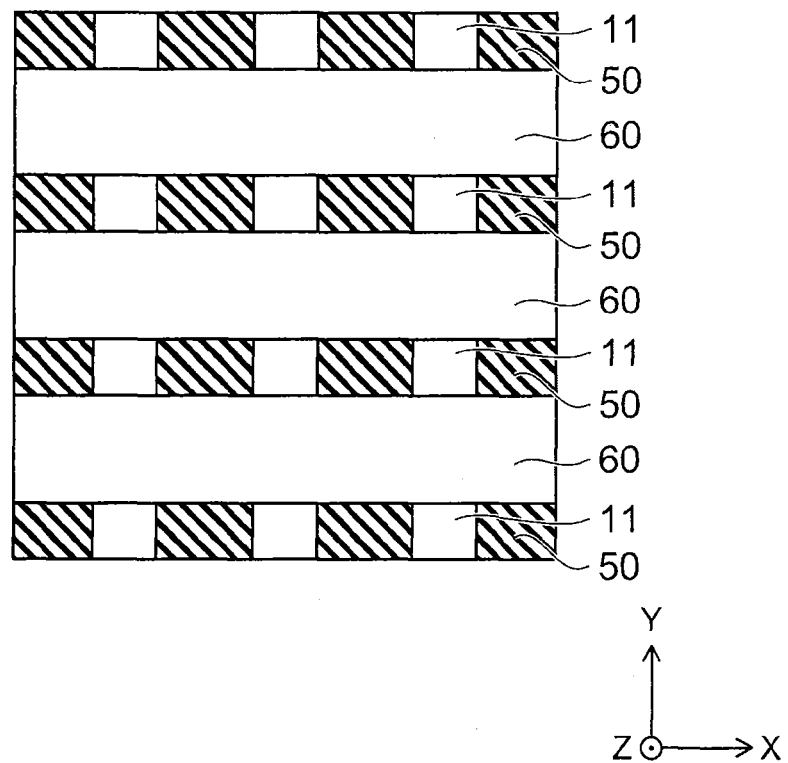


FIG. 11B



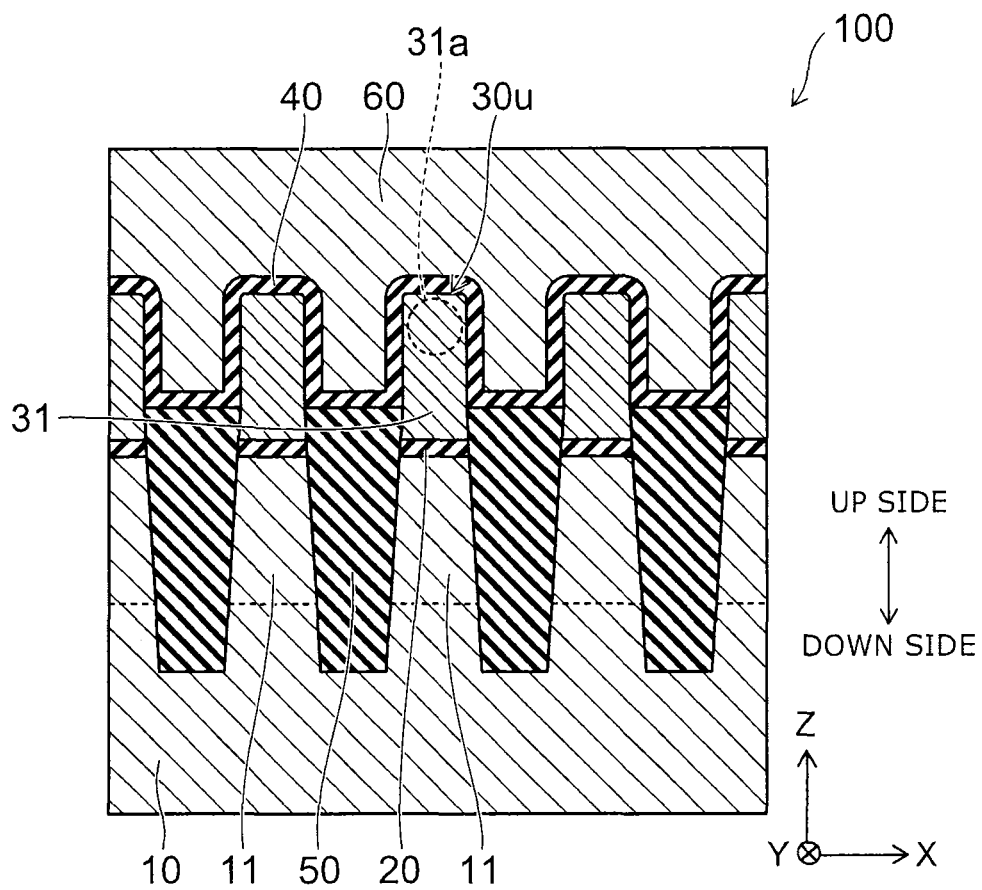


FIG. 12

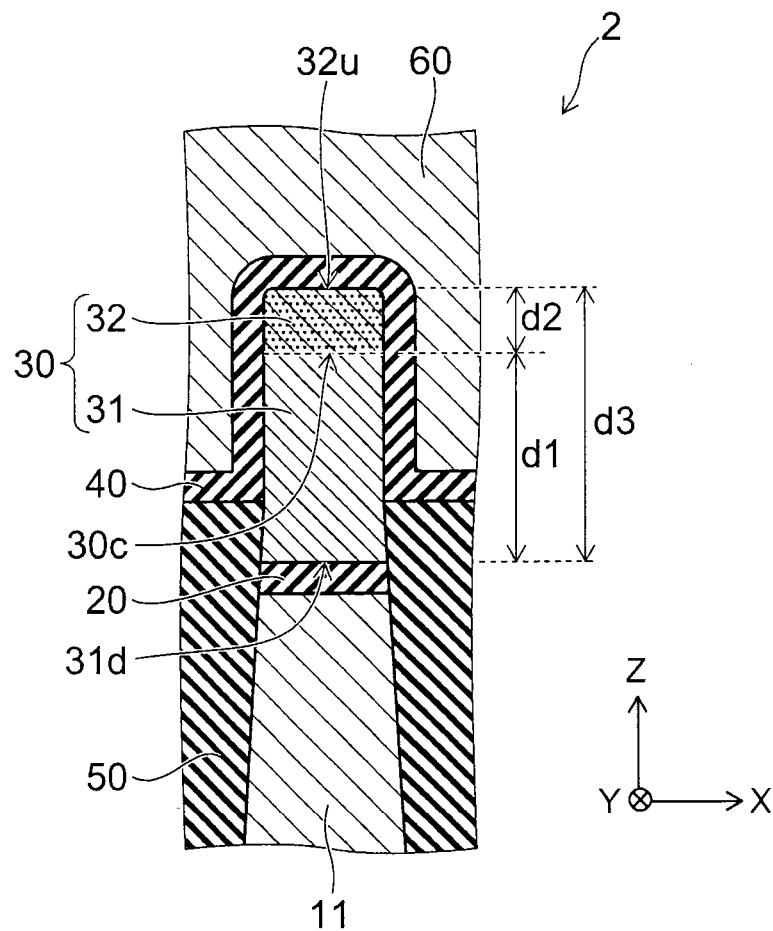
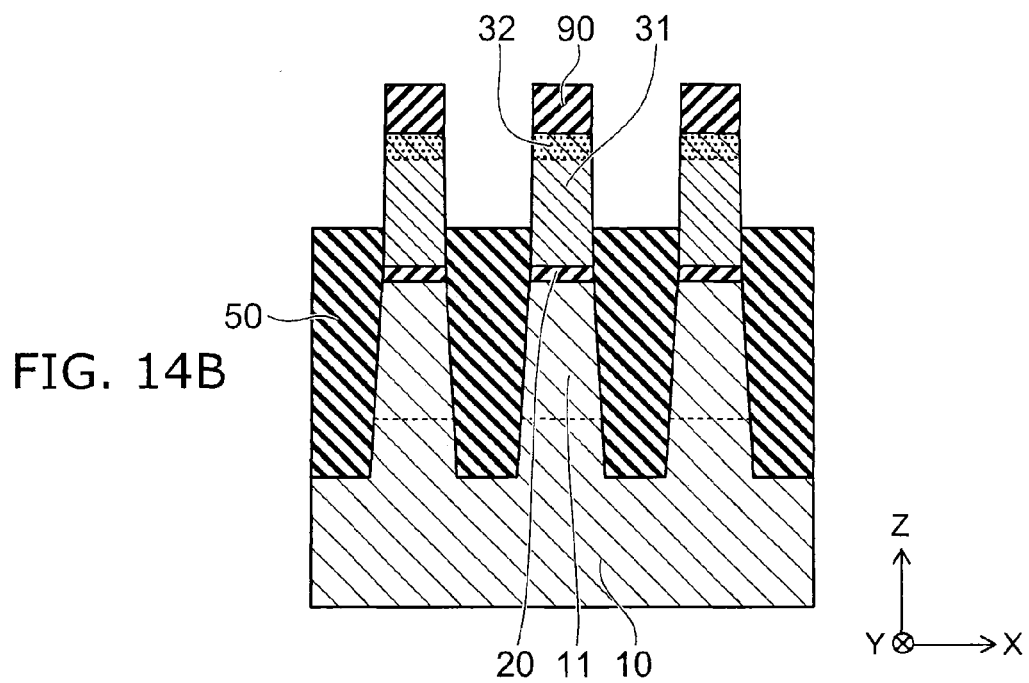
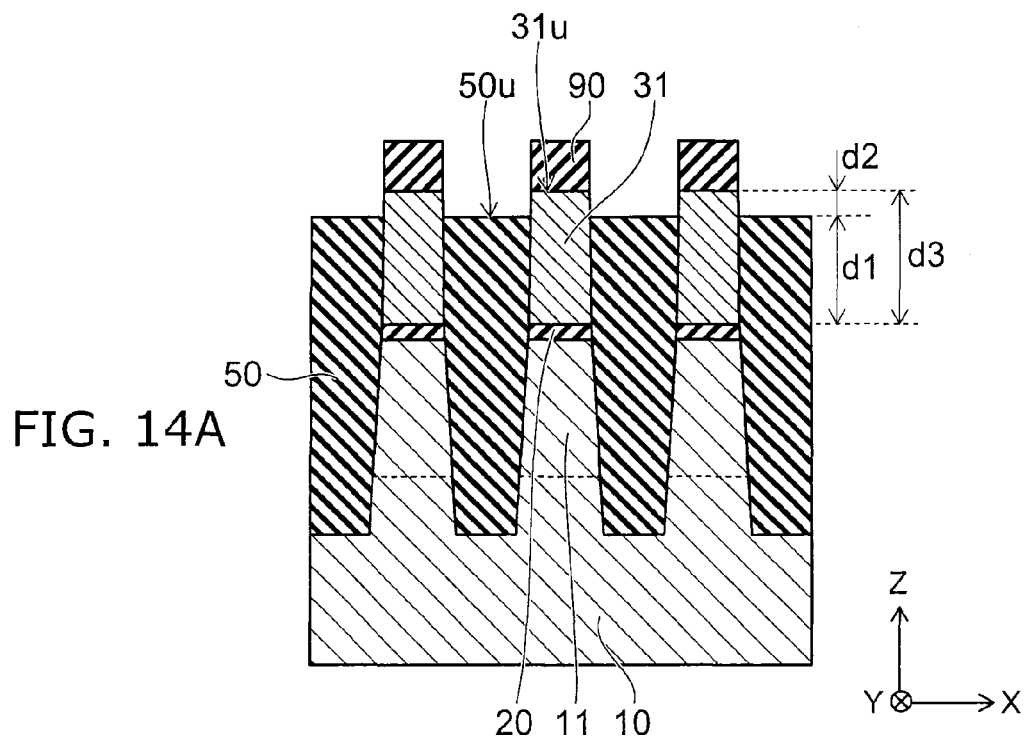


FIG. 13



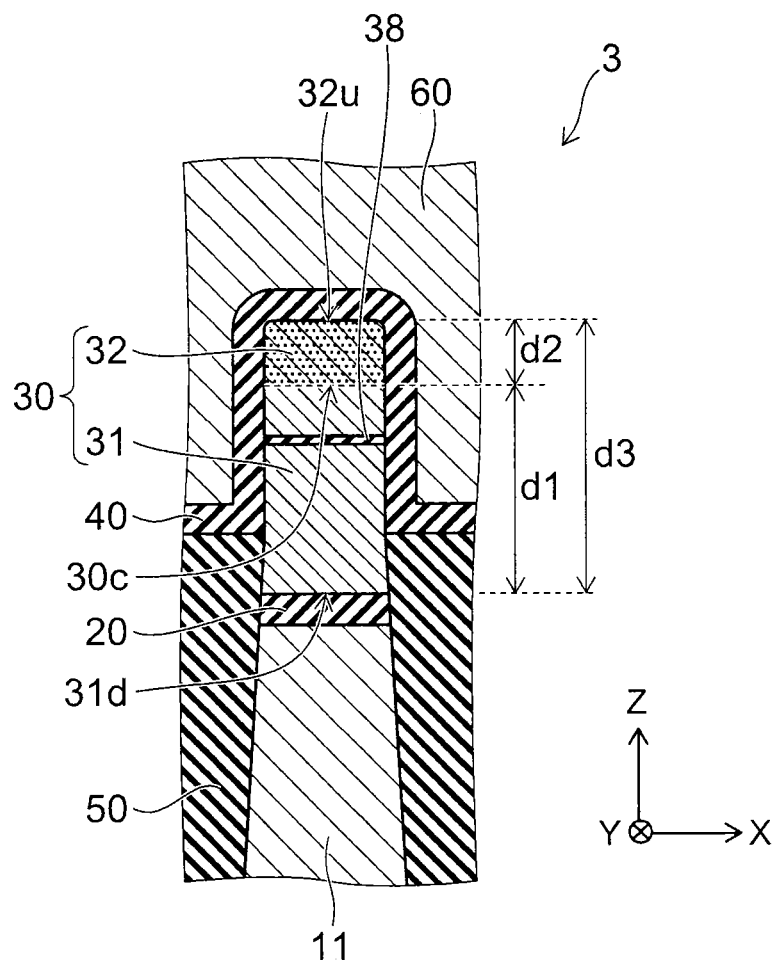


FIG. 15

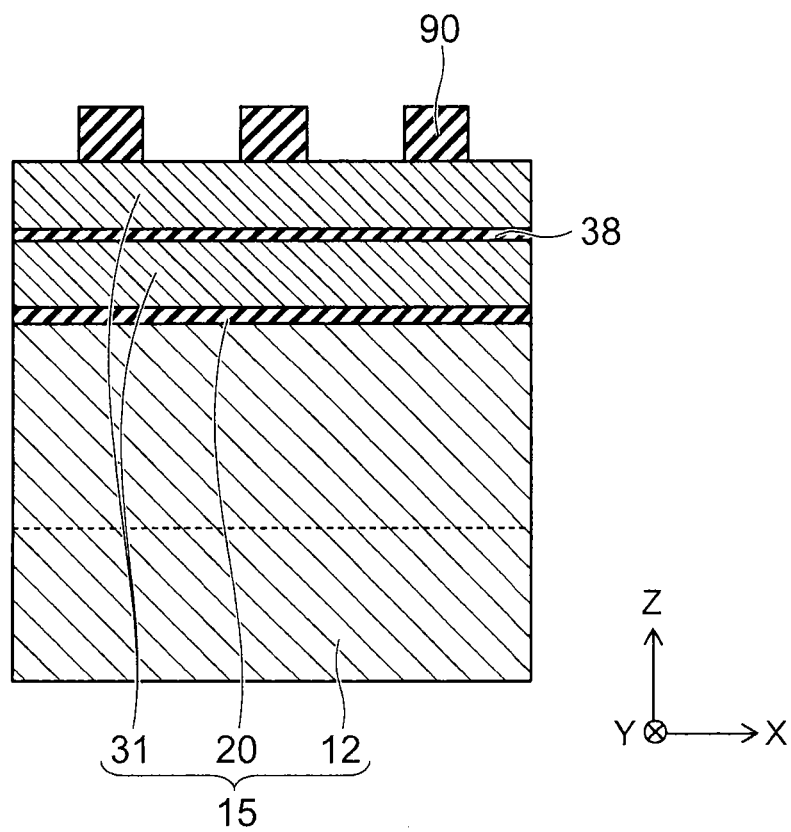
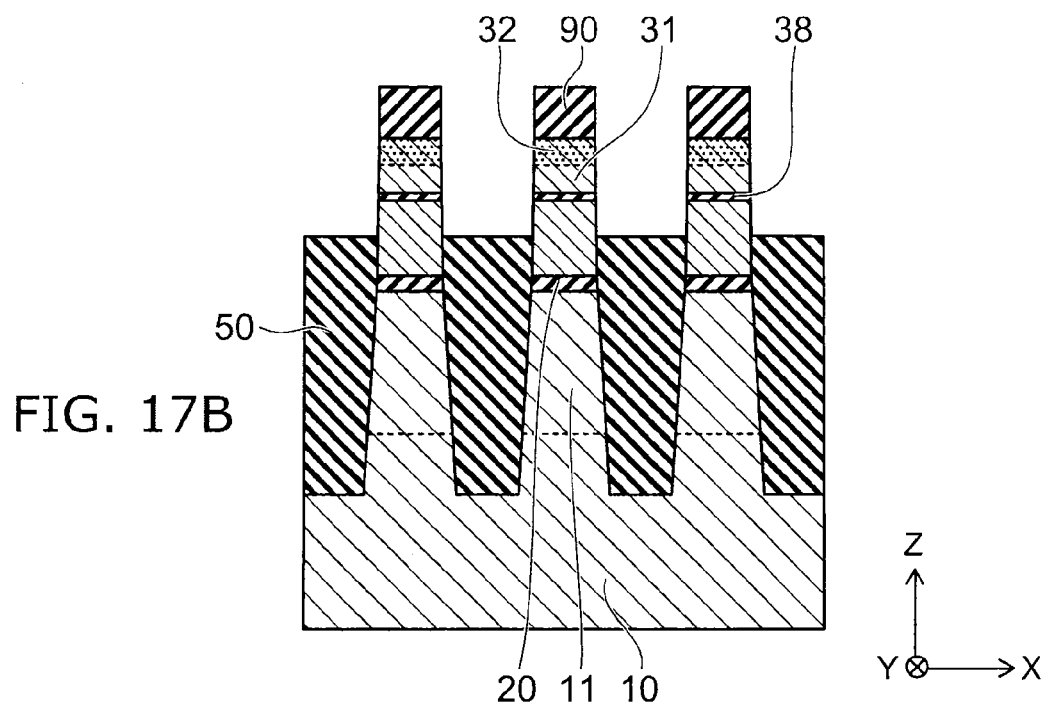
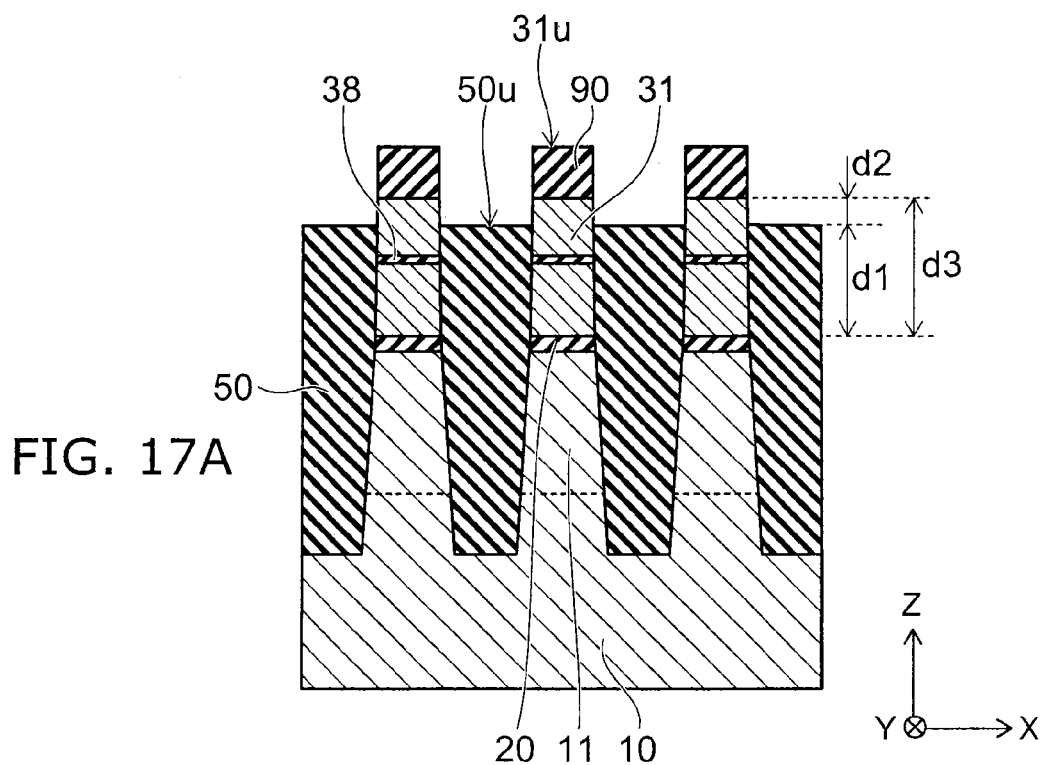


FIG. 16



1

NONVOLATILE SEMICONDUCTOR MEMORY DEVICE AND METHOD FOR MANUFACTURING SAME

CROSS-REFERENCE TO RELATED APPLICATIONS

This application is based upon and claims the benefit of priority from U.S. Provisional Patent Application 61/772,051, filed on Mar. 4, 2013; the entire contents of which are incorporated herein by reference.

FIELD

Embodiments described herein relate generally to a non-volatile semiconductor memory device and a method for manufacturing same.

BACKGROUND

In a nonvolatile semiconductor memory device typified by a NAND flash memory, while miniaturization is progressing, the element isolation region is configured to have a prescribed depth to ensure the electrical insulation between elements.

However, with the progress of miniaturization, the width of the floating gate becomes narrower. Hence, there is a problem that depletion of the upper portion of the floating gate is likely to occur and the stability of writing and the stability of reading are not sufficient. Thus, a nonvolatile semiconductor memory device is desired that is good in the stability of writing and the stability of reading even when miniaturization progresses.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a schematic plan view showing a nonvolatile semiconductor memory device according to a first embodiment;

FIG. 2A is a schematic cross-sectional view showing the nonvolatile semiconductor memory device in the position of line A-A' of FIG. 1, and FIG. 2B is a schematic cross-sectional view showing the nonvolatile semiconductor memory device in the position of line B-B' of FIG. 1;

FIG. 3 is an enlarged schematic cross-sectional view of a charge storage layer and the surroundings of the charge storage layer of FIG. 2A;

FIG. 4A to FIG. 11B are schematic views showing the manufacturing process of the nonvolatile semiconductor memory device according to the first embodiment;

FIG. 12 is a schematic cross-sectional view showing a nonvolatile semiconductor memory device according to a reference example;

FIG. 13 is a schematic cross-sectional view showing a nonvolatile semiconductor memory device according to a second embodiment;

FIG. 14A and FIG. 14B are schematic cross-sectional views showing the manufacturing process of the nonvolatile semiconductor memory device according to the second embodiment;

FIG. 15 is a schematic cross-sectional view showing a nonvolatile semiconductor memory device according to a third embodiment; and

FIG. 16 to FIG. 17B are schematic cross-sectional views showing the manufacturing process of the nonvolatile semiconductor memory device according to the third embodiment.

DETAILED DESCRIPTION

In general, according to one embodiment, a nonvolatile semiconductor memory device includes: a plurality of first

2

semiconductor regions extending in a first direction, and the plurality of first semiconductor regions being arranged in a direction crossing the first direction; a plurality of control gate electrodes provided on an upper side of the plurality of first semiconductor regions, the plurality of control gate electrodes extending in a second direction different from the first direction, and the plurality of control gate electrodes being arranged in a direction crossing the second direction; a charge storage layer provided in a position, and each of the plurality of first semiconductor regions and each of the plurality of control gate electrodes cross in the position; a first insulating film provided between the charge storage layer and each of the plurality of first semiconductor regions; a second insulating film provided between the charge storage layer and each of the plurality of control gate electrodes; and an element isolation region provided between adjacent ones of the plurality of first semiconductor regions, and the element isolation region being in contact with the first insulating film and a first portion of the charge storage layer on the first insulating film side.

Each of the plurality of control gate electrodes is in contact with a second portion other than the first portion of the charge storage layer via the second insulating film. The charge storage layer includes a silicon-containing layer in contact with the first insulating film and a silicide-containing layer provided on the silicon-containing layer.

Hereinbelow, embodiments are described with reference to the drawings. In the following description, identical components are marked with the same reference numerals, and a description of components once described is omitted as appropriate.

First Embodiment

FIG. 1 is a schematic plan view showing a nonvolatile semiconductor memory device according to a first embodiment.

FIG. 2A is a schematic cross-sectional view showing the nonvolatile semiconductor memory device in the position of line A-A' of FIG. 1, and FIG. 2B is a schematic cross-sectional view showing the nonvolatile semiconductor memory device in the position of line B-B' of FIG. 1. In FIG. 2A and FIG. 2B, the positive direction of the Z axis is set upward and the negative direction is set downward.

FIG. 3 is an enlarged schematic cross-sectional view of a charge storage layer and the surroundings of the charge storage layer of FIG. 2A.

As shown in FIG. 1, a nonvolatile semiconductor memory device 1 includes a plurality of semiconductor regions 11 (first semiconductor regions) and a plurality of control gate electrodes 60.

Each of the plurality of semiconductor regions 11 extends in the Y direction (a first direction). The plurality of semiconductor regions 11 are arranged in a direction (e.g. the X direction) crossing the Y direction. The conductivity type of the plurality of semiconductor regions 11 is, for example, the p type.

Each of the plurality of control gate electrodes 60 is provided on the upper side of the plurality of semiconductor regions 11. Each of the plurality of control gate electrodes 60 extends in the X direction (a second direction) different from the Y direction. The plurality of control gate electrodes 60 are arranged in a direction (e.g. the Y direction) crossing the X direction.

The plurality of control gate electrodes 60 are provided on the upper side of the plurality of semiconductor regions 11. In the nonvolatile semiconductor memory device 1, each of the

3

plurality of semiconductor regions **11** and each of the plurality of control gate electrodes **60** cross.

A transistor is disposed in the position where each of the plurality of semiconductor regions **11** and each of the plurality of control gate electrodes **60** cross. The transistor is described later. The transistors are arranged two-dimensionally in the X direction and the Y direction. Each transistor functions as a memory cell of the nonvolatile semiconductor memory device **1**.

As shown in FIG. 2A and FIG. 2B, the nonvolatile semiconductor memory device **1** includes the semiconductor region **11**, the control gate electrode **60**, a charge storage layer **30**, a gate insulating film **20** (a first insulating film), an IPD (inter poly dielectric) film **40** (a second insulating film), an element isolation region **50**, a semiconductor region **10**, and an insulating layer **70**. The conductivity type of the semiconductor region **10** is the n type. The charge storage layer **30** may be referred to as a floating gate layer **30**. The control gate electrode **60** may be referred to as a word line **60**. The IPD film **40** may be referred to as a charge block film **40**. The semiconductor region **10** and the semiconductor region **11** are collectively referred to as a semiconductor layer **12**.

In the nonvolatile semiconductor memory device **1**, the semiconductor region **11**, the gate insulating film **20**, the charge storage layer **30**, the IPD film **40**, and the control gate electrode **60** constitute a transistor. The transistor is provided in the position where the semiconductor region **11** and the control gate electrode **60** cross.

Each of the plurality of semiconductor regions **11** forms part of a NAND string. Each of the plurality of semiconductor regions **11** is separated by the element isolation region **50**. Each of the plurality of semiconductor regions **11** is defined by the element isolation region **50** in the semiconductor layer **12**. Each of the plurality of semiconductor regions **11** functions as an active area of the transistor.

The charge storage layer **30** is provided in the position where each of the plurality of semiconductor regions **11** and each of the plurality of control gate electrodes **60** cross. The charge storage layer **30** is in a rectangular shape extending in the Z direction in the A-A' cross section and the B-B' cross section shown in FIG. 2A and FIG. 2B. Thus, the charge storage layer **30** has a prismatic shape extending in the Z direction. The charge storage layer **30** can store a charge that has tunneled from the semiconductor region **11** via the gate insulating film **20**.

Here, the charge storage layer **30** includes a silicon-containing layer **31** in contact with the gate insulating film **20** and a silicide-containing layer **32** provided on the silicon-containing layer **31**.

The resistivity of the silicide-containing layer **32** is lower than the resistivity of the silicon-containing layer **31**. The silicon-containing layer **31** includes, for example, a polysilicon (poly-Si) layer doped with an impurity element such as boron (B). The silicide-containing layer **32** includes a layer of a silicide made out of polysilicon doped with an impurity element such as boron (B). As the metal for making a silicide out of polysilicon, for example, at least one metal selected from titanium (Ti), nickel (Ni), cobalt (Co), molybdenum (Mo), and tungsten (W) is given.

The length from the lower end **31d** of the silicon-containing layer **31** to the upper end **50u** of the element isolation region **50** is the same as the length from the lower end **31d** of the silicon-containing layer **31** to the junction **30c** between the silicon-containing layer **31** and the silicide-containing layer **32** (corresponding to the thickness of the silicon-containing layer **31** in the Z direction). For example, the height of

4

the upper end **50u** of the element isolation region **50** is the same as the height of the junction **30c**.

The width of the silicide-containing layer **32** in a direction (e.g. the X direction) crossing the Y direction is, for example, 5 nm (nanometers) or less.

The gate insulating film **20** is provided between the charge storage layer **30** and each of the plurality of semiconductor regions **11**. The gate insulating film **20** functions as a tunnel insulating film through which a charge (e.g. electrons) tunnels between the semiconductor region **11** and the charge storage layer **30**.

The IPD film **40** is provided between the charge storage layer **30** and each of the plurality of control gate electrodes **60**. The element isolation region **50** is provided between adjacent ones of the plurality of semiconductor regions **11**. The IPD film **40** covers the upper surface **30u** of the charge storage layer **30**. The IPD film **40** further covers part of the side wall **32w** of the charge storage layer **30**.

Each of the plurality of control gate electrodes **60** is in contact with the charge storage layer **30** via the IPD film **40**. For example, as shown in FIG. 2A, the control gate electrode **60** is in contact with, via the IPD film **40**, a portion of the charge storage layer **30** other than a portion of the charge storage layer **30** with which the element isolation region **50** is in contact. In other words, each of the plurality of control gate electrodes **60** has an extending portion **60a** in contact with the charge storage layer **30** via the IPD film **40**. Adjacent ones of the plurality of extending portions **60a** sandwiches the charge storage layer **30**.

That is, the control gate electrode **60** covers part of the charge storage layer **30** via the IPD film **40**. For example, the control gate electrode **60** covers the upper surface **30u** and part of the side wall **32w** of the charge storage layer **30** via the IPD film **40** (see FIG. 2A). The control gate electrode **60** covers the upper surface **30u** of the charge storage layer **30** via the IPD film **40** (see FIG. 2B). The control gate electrode **60** functions as a gate electrode for controlling the transistor.

The element isolation region **50** is in contact with the gate insulating film **20** and a portion of the charge storage layer **30** on the gate insulating film **20** side. The element isolation region **50** is further in contact with the semiconductor region **10**. The insulating layer **70** is provided between adjacent ones of the plurality of control gate electrodes **60**. The insulating layer **70** is in contact with the IPD film **40**, the charge storage layer **30**, and the gate insulating film **20**. For example, as shown in FIG. 2B, the insulating layer **70** covers the side wall **32w** of the charge storage layer **30**.

That is, the upper surface **30u** and the side wall **32w** of the charge storage layer **30** are covered with an insulator including the IPD film **40** and the insulating layer **70**. Thereby, the charge stored in the charge storage layer **30** is prevented from leaking to the control gate electrode **60**.

The material of the semiconductor region **11** is silicon doped with boron (B) and/or the like. The material of the semiconductor region **10** is silicon doped with phosphorus (P), arsenic (As), and/or the like. The gate insulating film **20** may be a NON film like that shown in FIG. 3 in which a silicon nitride film **20a**, a silicon oxide film **20b**, and a silicon nitride film **20c** are stacked in this order, or may be a single-layer film of a silicon oxide film or a silicon nitride film. The illustration of the gate insulating film **20** is only an example, and the gate insulating film **20** is not limited to this structure.

The material of the element isolation region **50** and the insulating layer **70** is, for example, silicon oxide (SiO₂). The material of the control gate electrode **60** is, for example, polysilicon containing a p-type impurity. Alternatively, the

5

material of the control gate electrode **60** may be a metal such as tungsten, a metal silicide, or the like.

As shown in FIG. 3, the upper end **32u** and the side wall **32w** of the silicide-containing layer **32** are covered by the IPD film **40**. The IPD film **40** includes a nitride film **40a** (a second nitride film) in contact with the silicide-containing layer **32**, an oxide film **40b** covering the nitride film **40a**, and a nitride film **40c** covering the oxide film **40b**.

The material of the nitride film **40a** is titanium silicon nitride (SiTiN), titanium nitride (TiN), or the like. The material of the oxide film **40b** is silicon oxide (SiO₂) or the like. The material of the nitride film **40c** is silicon nitride (SiN) or the like.

In the embodiment, the p type may be taken as a first conductivity type and the n type may be taken as a second conductivity type, or the n type may be taken as the first conductivity type and the p type may be taken as the second conductivity type. As the p-type impurity element, for example, boron (B) is given. As the n-type impurity element, for example, phosphorus (P) and arsenic (As) are given.

The manufacturing process of the nonvolatile semiconductor memory device **1** will now be described.

The method for forming films and layers described below is, unless otherwise specified, appropriately selected from CVD (chemical vapor deposition), the sputtering method, the ALD (atomic layer deposition) method, the epitaxial method, the spin coating method, etc. The removal of films and layers is appropriately selected from dry etching such as RIE (reactive ion etching), wet etching using a hydrofluoric acid solution, an alkaline solution, or the like, and ashing using an oxygen-containing gas.

FIG. 4A to FIG. 11B are schematic views showing the manufacturing process of the nonvolatile semiconductor memory device according to the first embodiment.

Of FIG. 4A to FIG. 11B, the drawings of the numbers including "A" show a cross section corresponding to line A-A' of FIG. 1, and the drawings of the numbers including "B" show a plan view.

First, as shown in FIG. 4A and FIG. 4B, a stacked body **15** is prepared. The stacked body **15** includes the semiconductor layer **12**, the gate insulating film **20** provided on the semiconductor layer **12**, and the silicon-containing layer **31** provided on the gate insulating film **20**. The stacking direction of the stacked body **15** is the Z direction. Subsequently, a plurality of mask layers **90** extending in the Y direction and arranged in a direction (e.g. the X direction) crossing the Y direction are formed on the stacked body **15**.

The patterning of the mask layer **90** is performed by, for example, photolithography and etching. As the material of the mask layer **90**, a material having a high processing selectivity to the semiconductor is selected. For example, the material of the mask layer **90** is silicon oxide (SiO₂), silicon nitride (SiN), a resist, a material other than these, or a material in which these materials are stacked.

Next, as shown in FIG. 5A and FIG. 5B, etching is performed on the stacked body **15** exposed from the plurality of mask layers **90**. Thereby, a plurality of trenches **80** extending in the Y direction are formed in the semiconductor layer **12**. Consequently, the semiconductor region **11** sandwiched by adjacent ones of the plurality of trenches **80** is formed. The width of the silicide-containing layer **32** in the X direction is adjusted to 5 nm or less. The gate insulating film **20** extending in the Y direction is formed on the semiconductor region **11**, and the silicon-containing layer **31** extending in the Y direction is formed on the gate insulating film **20**.

6

Next, as shown in FIG. 6A and FIG. 6B, the element isolation region **50** is formed in each of the plurality of trenches **80**.

Next, as shown in FIG. 7A and FIG. 7B, the element isolation region **50** is etched back. Thereby, the element isolation region **50** in contact with the semiconductor region **11**, the gate insulating film **20**, and a portion of the silicon-containing layer **31** on the gate insulating film **20** side is formed in each of the plurality of trenches **80**. After that, the mask layer **90** is removed. Then, the natural oxide film formed on the surface of the silicon-containing layer **31** is removed.

Next, the portion exposed from the element isolation region **50** of the silicon-containing layer **31** is exposed to a metal element-containing gas **35**. Then, the silicon-containing layer **31** is heated. FIG. 8A and FIG. 8B show the state after the silicon-containing layer **31** is exposed to the metal element-containing gas **35**.

As the metal element-containing gas **35**, for example, a metal chloride is used. As the metal chloride, for example, titanium tetrachloride (TiCl₄) is given. As the metal chloride, also a chloride of at least one metal selected from nickel (Ni), cobalt (Co), molybdenum (Mo), and tungsten (W) may be used. The heating temperature is not less than 500° C. and not more than 600° C.

The metal (e.g. Ti) in the metal chloride selectively reacts more with the silicon-containing layer **31** than with the element isolation region **50**. Consequently, part of the silicon-containing layer **31** is made into a silicide. That is, the charge storage layer **30** including the silicon-containing layer **31** and the silicide-containing layer **32** is formed on the gate insulating film **20**. In the case where titanium tetrachloride is used, the silicide-containing layer **32** contains, for example, titanium silicide (TiSi).

Subsequently, after part of the silicon-containing layer **31** is made into a silicide, the silicon-containing layer that has become a silicide is exposed to a nitrogen-containing gas. Thereby, the surface of the charge storage layer **30** exposed from the element isolation region **50** is nitrified (see the nitride film **40a** of FIG. 3). Then, the oxide film **40b** and the nitride film **40c** are formed. Thereby, the IPD film **40** including the nitride film **40a**, the oxide film **40b**, and the nitride film **40c** is formed. FIG. 9A and FIG. 9B show this state.

As shown in FIG. 9A and FIG. 9B, the portion exposed from the element isolation region **50** of the charge storage layer **30** is covered by the IPD film **40**.

Next, as shown in FIG. 10A and FIG. 10B, a control gate electrode layer **60L** is formed in each of the plurality of trenches **80** and on the charge storage layer **30** via the IPD film **40**.

Next, as shown in FIG. 11A and FIG. 11B, the control gate electrode layer **60L** is divided into a plurality of control gate electrodes **60**. The control gate electrode layer **60L** is divided by photolithography and etching. After the division, the plurality of control gate electrodes **60** extend in the X direction, and are arranged in the Y direction. After that, the insulating layer **70** is formed on the semiconductor region **11** between adjacent ones of the plurality of control gate electrodes **60** (see FIG. 2B). By such a manufacturing process, the nonvolatile semiconductor memory device **1** is formed.

FIG. 12 is a schematic cross-sectional view showing a nonvolatile semiconductor memory device according to a reference example.

In a nonvolatile semiconductor memory device **100** according to the reference example, the charge storage layer is a single layer. The charge storage layer of the reference example is formed of the silicon-containing layer **31**.

A case is assumed where, for example, in the nonvolatile semiconductor memory device **100**, miniaturization has progressed and the width in the X direction of the silicon-containing layer **31** has become minute (e.g. 5 nm or less).

In this case, for example, when in the time of the writing of data a positive potential is applied to the control gate electrode **60** and a negative potential (or the ground potential) is applied to the semiconductor region **11**, depletion is likely to occur in the upper portion **31a** of the silicon-containing layer **31**. This is because the silicon-containing layer **31** is very fine and the electric field is likely to concentrate at the upper end of the silicon-containing layer **31**.

There are few carriers in the depletion layer. Therefore, in the time of the writing of data, an insulating layer of the thicknesses of the IPD film **40** and the depletion layer (the upper portion **31a**) exists on the silicon-containing layer **31**. In other words, in the time of the writing of data, the substantial thickness of the silicon-containing layer **31** is the thickness excluding that of the depletion layer (the upper portion **31a**). That is, a charge cannot be stored in the portion where the depletion layer is formed.

Therefore, in the nonvolatile semiconductor memory device **100**, the silicon-containing layer **31** cannot be made to sufficiently function as a charge storage layer, and the stability of data writing is not sufficient. Furthermore, also in the time of data reading, depletion in the upper portion **31a** of the silicon-containing layer **31** is likely to occur, and the stability of data reading is not sufficient. For example, a Vth jump phenomenon may occur in which the threshold voltage (Vth) in data reading rises steeply. Thus, it is preferable to suppress the depletion in the upper portion of the charge storage layer.

As a first means for suppressing the depletion in the upper portion of the charge storage layer, there may be a means in which the concentration of the impurity element contained in the charge storage layer is increased. This is because the increase in the impurity element concentration decreases the resistivity of the charge storage layer and suppresses the extension of the depletion layer.

For example, there is a means in which a high concentration impurity element is introduced into the upper portion of the charge storage layer by plasma doping. However, when plasma is used, the very fine charge storage layer is damaged and a good quality charge storage layer is not formed.

As a second means, there may be a means in which the silicon-containing layer **31** of the stacked body **15** is replaced with a metal layer (or a silicide layer). That is, it is a means in which a stacked body composed of the semiconductor layer **12**/the gate insulating film **20**/a metal layer (or a silicide layer) is prepared before the trench **80** is formed. By this means, the charge storage layer is made of a metal (or a silicide), and it can be foreseen that the depletion in the upper portion of the charge storage layer will be suppressed.

However, when this means is employed, during forming the trench **80**, the metal or silicide that is a component of the charge storage layer may go through the trench **80** to adhere to the semiconductor regions **10** and **11** as a residue, and the attached metal or silicide may diffuse into the semiconductor regions **10** and **11**. Consequently, the electric conductivity, conductivity type, etc. of the semiconductor regions **10** and **11** may be changed to cause a loss to the function as an active area of the semiconductor region **11**.

In contrast, in the first embodiment, the lower side of the charge storage layer **30** is formed of the silicon-containing layer **31** and the upper side of the charge storage layer **30** is formed of the silicide-containing layer **32**. The resistivity of the silicide-containing layer **32** is lower than the resistivity of the silicon-containing layer **31**. Therefore, in the time of data

writing and reading, the depletion in the upper portion of the charge storage layer **30** is suppressed. Thus, data writing and reading are stabilized.

The formation of the silicide-containing layer **32** is performed not by plasma doping but by a thermal reaction. Therefore, the charge storage layer **30** is less likely to be damaged in the process and a good quality charge storage layer is formed. Furthermore, the silicide-containing layer **32** is a silicide (self aligned silicide) layer formed by exposing the silicon-containing layer **31** to a reaction gas. Therefore, even when miniaturization progresses by generations, the process of making a silicide follows the miniaturization by generations. Consequently, a charge storage layer with a narrow pitch and a very fine size is formed by generations.

In the first embodiment, the stacked body **15** before forming the trench **80** only includes the silicon-containing layer **31**. Hence, when the trench **80** is formed, there is no case where a metal or a silicide adheres to the semiconductor regions **10** and **11** as a residue. Even if a component of the silicon-containing layer **31** adheres to the semiconductor regions **10** and **11**, there is no problem because the main component of the silicon-containing layer **31** and the main component of the semiconductor regions **10** and **11** are both the same silicon (Si). Thereby, the electric conductivity, conductivity type, etc. of the semiconductor regions **10** and **11** are less likely to be changed, and the function as an active area of the semiconductor region **11** is not lost.

In the nonvolatile semiconductor memory device **1**, not only is the control gate electrode **60** in contact with the upper end of the charge storage layer **30** via the IPD film **40**, but the control gate electrode **60** is also in contact with the side wall **32w** of the charge storage layer **30** via the IPD film **40**. Thus, the charge storage state of the charge storage layer **30** is evenly reflected on the control gate electrode **60**.

Before the insulating layer **70** is buried, infrastructure processing for forming the source/drain is performed. The source/drain regions are not shown.

Second Embodiment

FIG. **13** is a schematic cross-sectional view showing a nonvolatile semiconductor memory device according to a second embodiment.

FIG. **13** is an enlarged schematic cross-sectional view of the charge storage layer and the surroundings of the charge storage layer.

The basic structure of a nonvolatile semiconductor memory device **2** is the same as the basic structure of the nonvolatile semiconductor memory device **1**. However, the ratio between the thickness of the silicon-containing layer **31** and the thickness of the silicide-containing layer **32** is different from the ratio between the thickness of the silicon-containing layer **31** and the thickness of the silicide-containing layer **32** in the nonvolatile semiconductor memory device **1**.

In the nonvolatile semiconductor memory device **2**, the length d1 from the lower end **31d** of the silicon-containing layer **31** to the junction **30c** between the silicon-containing layer **31** and the silicide-containing layer **32** is longer than the length d2 from the junction **30c** to the upper end **32u** of the silicide-containing layer **32** (corresponding to the thickness of the silicide-containing layer **32** in the Z direction). That is, the thickness in the Z direction of the silicon-containing layer **31** is thicker than the thickness in the Z direction of the silicide-containing layer **32**.

For example, the length d2 is not less than 10% and not more than 20% of the length d3 from the lower end of the charge storage layer **30** (corresponding to the lower end **31d**

of the silicon-containing layer 31) to the upper end of the charge storage layer 30 (the upper end 32u of the silicide-containing layer 32). That is, the thickness in the Z direction of the silicide-containing layer 32 is not less than 10% and not more than 20% of the thickness in the Z direction of the charge storage layer 30. The length d2 is set to, for example, the thickness in the Z direction of the depletion layer in the reference example.

FIG. 14A and FIG. 14B are schematic cross-sectional views showing the manufacturing process of the nonvolatile semiconductor memory device according to the second embodiment.

The manufacturing process of the nonvolatile semiconductor memory device 2 is basically the same as the manufacturing process of the nonvolatile semiconductor memory device 1. However, in the manufacturing process of the nonvolatile semiconductor memory device 2, the etchback of the element isolation region 50 is performed at least two times. That is, the etchback of the element isolation region 50 includes the first etchback processing and the second etchback processing.

For example, the first etchback processing is performed from the state of FIG. 6A and FIG. 6B. Thereby, the element isolation region 50 shown in FIG. 14A is obtained. In this stage, the upper end 50u of the element isolation region 50 is located at a depth of d2 from the upper end 31u of the silicon-containing layer 31.

The length d2 in the Z direction of the portion of the silicon-containing layer 31 exposed from the element isolation region 50 by the first etchback processing is shorter than the length d1 in the Z direction of the portion of the silicon-containing layer 31 not exposed from the element isolation region 50.

For example, the length d2 in the Z direction of the portion of the silicon-containing layer 31 exposed from the element isolation region 50 by the first etchback processing is adjusted to not less than 10% and not more than 20% of the length in the Z direction of the silicon-containing layer 31.

Subsequently, after the first etchback processing, the portion exposed from the element isolation region 50 of the silicon-containing layer 31 is exposed to a metal element-containing gas (e.g. TiCl_4). Thereby, a portion of the silicon-containing layer 31 extending approximately d2 in depth from the upper end 31u of the silicon-containing layer 31 is changed into the silicide-containing layer 32.

After that, the second etchback processing is performed on the element isolation region 50. FIG. 14B shows this state. In this stage, the element isolation region 50 in contact with the semiconductor region 11, the gate insulating film 20, and a portion of the silicon-containing layer 31 on the gate insulating film 20 side is formed. After that, the IPD film 40 is formed. By such a manufacturing process, the nonvolatile semiconductor memory device 2 is formed.

In the nonvolatile semiconductor memory device 2, since the portion where the depletion layer is formed in the reference example is replaced with the silicide-containing layer 32, depletion can be suppressed similarly to the nonvolatile semiconductor memory device 1. The nonvolatile semiconductor memory device 2 exhibits similar effects to the nonvolatile semiconductor memory device 1. In addition, the nonvolatile semiconductor memory device 2 exhibits the following effect.

The resistivity of the silicide-containing layer 32 is lower than the resistivity of the silicon-containing layer 31. Therefore, after data writing, electrons are preferentially stored more in the silicide-containing layer 32 than in the silicon-containing layer 31.

In the nonvolatile semiconductor memory device 2, the junction 30c between the silicon-containing layer 31 and the silicide-containing layer 32 is located more on the upper side than in the nonvolatile semiconductor memory device 1. In other words, in the nonvolatile semiconductor memory device 2, the junction 30c is located more on the upper side than in the nonvolatile semiconductor memory device 1. The silicide-containing layer 32 of the nonvolatile semiconductor memory device 2 is more away from the semiconductor region 11 than the silicide-containing layer 32 of the nonvolatile semiconductor memory device 1.

Therefore, in the nonvolatile semiconductor memory device 2, after data writing, electrons stored in the silicide-containing layer 32 are less likely to be released to the semiconductor region 11. That is, the data retention ability of the nonvolatile semiconductor memory device 2 is further increased as compared to the data retention ability of the nonvolatile semiconductor memory device 1.

Third Embodiment

FIG. 15 is a schematic cross-sectional view showing a nonvolatile semiconductor memory device according to a third embodiment.

The basic structure of a nonvolatile semiconductor memory device 3 is the same as the basic structure of the nonvolatile semiconductor memory device 2. However, the charge storage layer 30 of the nonvolatile semiconductor memory device 3 includes a nitride film 38 (a first nitride film). The nitride film (SiN) 38 is provided on the lower side of the silicide-containing layer 32. Although FIG. 15 illustrates a state where the silicide-containing layer 32 and the nitride film 38 are apart, the nitride film 38 may be in contact with the silicide-containing layer 32.

The nitride film 38 functions as a barrier film that suppresses the diffusion of the impurity element (e.g. boron) contained in the silicon-containing layer 31 to the silicide-containing layer 32. The thickness of the nitride film 38 is so adjusted that electrons can pass through the nitride film 38. The thickness of the nitride film 38 is, for example, in the order of atoms.

FIG. 16 to FIG. 17B are schematic cross-sectional views showing the manufacturing process of the nonvolatile semiconductor memory device according to the third embodiment.

First, as shown in FIG. 16, the stacked body 15 including the silicon-containing layer 31 including the nitride film 38 is prepared. In the stacked body 15, the silicon-containing layer 31 is provided on the upper and lower sides of the nitride film 38. After that, the processes described in FIG. 5 and FIG. 6 are performed.

Next, as shown in FIG. 17A and FIG. 17B, the etchback of the element isolation region 50 is performed at least two times.

For example, the first etchback processing is performed. Thereby, the element isolation region 50 shown in FIG. 17A is obtained. In this stage, the upper end 50u of the element isolation region 50 is located at a depth of d2 from the upper end 31u of the silicon-containing layer 31.

The length d2 in the Z direction of the portion of the silicon-containing layer 31 exposed from the element isolation region 50 by the first etchback processing is shorter than the length d1 in the Z direction of the portion of the silicon-containing layer 31 not exposed from the element isolation region 50. The position of the upper end 50u of the element isolation region 50 is adjusted to a position higher than the position of the nitride film 38.

11

Subsequently, after the first etchback processing, the portion exposed from the element isolation region 50 of the silicon-containing layer 31 is exposed to a metal element-containing gas (e.g. TiCl_4). A portion of the silicon-containing layer 31 on the upper side of the nitride film 38 is exposed to the metal element-containing gas. Thereby, a portion of the silicon-containing layer 31 extending approximately d2 in depth from the upper end 31u of the silicon-containing layer 31 is changed into the silicide-containing layer 32.

After that, the second etchback processing is performed on the element isolation region 50. FIG. 17B shows this state. In this stage, the element isolation region 50 in contact with the semiconductor region 11, the gate insulating film 20, and a portion of the silicon-containing layer 31 on the gate insulating film 20 side is formed. After that, the IPD film 40 is formed. By such a manufacturing process, the nonvolatile semiconductor memory device 3 is formed.

Also in the nonvolatile semiconductor memory device 3, similar effects to the nonvolatile semiconductor memory device 2 are exhibited. In addition, the nonvolatile semiconductor memory device 3 exhibits the following effects.

A case is assumed where, for example, titanium (Ti) is contained in the silicide-containing layer 32. In this case, due to the affinity between titanium and boron (B) contained in the silicon-containing layer 31, the silicide-containing layer 32 may absorb boron in the silicon-containing layer 31 to form titanium boride (TiB) in the silicide-containing layer 32. The titanium boride exhibits insulating properties, and the resistivity of the silicide-containing layer 32 may be increased. Thus, it is preferable to suppress the diffusion of boron from the silicon-containing layer 31 to the silicide-containing layer 32.

In the nonvolatile semiconductor memory device 3, the nitride film 38 functioning as a barrier film is provided on the lower side of the silicide-containing layer 32. Therefore, the diffusion of boron from the silicon-containing layer 31 to the silicide-containing layer 32 is suppressed by the nitride film 38.

In the nonvolatile semiconductor memory device 3, by providing the nitride film 38, the impurity concentration of the silicon-containing layer 31 can be increased as compared to the impurity concentration of the silicon-containing layer 31 of the nonvolatile semiconductor memory devices 1 and 2. This means, to the electrons stored in the silicide-containing layer 32, that the barrier at the junction 30c becomes higher. Consequently, electrons stored in the silicide-containing layer 32 after writing are less likely to diffuse to the semiconductor region 11, and the data retention ability is further increased.

Hereinabove, embodiments are described with reference to specific examples. However, the embodiment is not limited to these specific examples. That is, one skilled in the art may appropriately make design modifications to these specific examples, and such modifications also are included in the scope of the embodiment to the extent that the spirit of the embodiment is included. The components of the specific examples described above and the arrangement, material, conditions, shape, size, etc. thereof are not limited to those illustrated but may be appropriately altered.

The term "on" in "a portion A is provided on a portion B" refers to the case where the portion A is provided on the portion B such that the portion A is in contact with the portion B and the case where the portion A is provided above the portion B such that the portion A is not in contact with the portion B.

Furthermore, components of the embodiments described above may be combined within the extent of technical feasi-

12

bility, and combinations of them also are included in the scope of the embodiment to the extent that the spirit of the embodiment is included. Furthermore, one skilled in the art may arrive at various alterations and modifications within the idea of the embodiment. Such alterations and modifications should be seen as within the scope of the embodiment.

While certain embodiments have been described, these embodiments have been presented by way of example only, and are not intended to limit the scope of the inventions. Indeed, the novel embodiments described herein may be embodied in a variety of other forms; furthermore, various omissions, substitutions and changes in the form of the embodiments described herein may be made without departing from the spirit of the inventions. The accompanying claims and their equivalents are intended to cover such forms or modifications as would fall within the scope and spirit of the invention.

What is claimed is:

1. A nonvolatile semiconductor memory device comprising:

a plurality of first semiconductor regions extending in a first direction, the plurality of first semiconductor regions being arranged in a direction crossing the first direction;

a plurality of control gate electrodes provided on an upper side of the plurality of first semiconductor regions, the plurality of control gate electrodes extending in a second direction different from the first direction, and the plurality of control gate electrodes being arranged in a direction crossing the second direction;

a charge storage layer provided in a position, each of the plurality of first semiconductor regions and each of the plurality of control gate electrodes cross in the position; a first insulating film provided between the charge storage layer and each of the plurality of first semiconductor regions;

a second insulating film provided between the charge storage layer and each of the plurality of control gate electrodes; and

an element isolation region provided between adjacent ones of the plurality of first semiconductor regions, the element isolation region being in contact with the first insulating film and a first portion of the charge storage layer on the first insulating film side,

each of the plurality of control gate electrodes being in contact with a second portion other than the first portion of the charge storage layer via the second insulating film, the charge storage layer including a silicon-containing layer in contact with the first insulating film and a silicide-containing layer provided on the silicon-containing layer, and

a length from a lower end of the silicon-containing layer to an upper end of the element isolation region being the same as a length from the lower end of the silicon-containing layer to a junction between the silicon-containing layer and the silicide-containing layer.

2. The device according to claim 1, wherein a width of the silicide-containing layer in the direction crossing the first direction is 5 nm (nanometers) or less.

3. A nonvolatile semiconductor memory device comprising:

a plurality of first semiconductor regions extending in a first direction, the plurality of first semiconductor regions being arranged in a direction crossing the first direction;

a plurality of control gate electrodes provided on an upper side of the plurality of first semiconductor regions, the

13

plurality of control gate electrodes extending in a second direction different from the first direction, and the plurality of control gate electrodes being arranged in a direction crossing the second direction;

a charge storage layer provided in a position, each of the plurality of first semiconductor regions and each of the plurality of control gate electrodes crossing in the position;

a first insulating film provided between the charge storage layer and each of the plurality of first semiconductor regions;

a second insulating film provided between the charge storage layer and each of the plurality of control gate electrodes; and

an element isolation region provided between adjacent ones of the plurality of first semiconductor regions, the element isolation region being in contact with the first insulating film and a first portion of the charge storage layer on the first insulating film side,

14

each of the plurality of control gate electrodes being in contact with a second portion other than the first portion of the charge storage layer via the second insulating film, the charge storage layer including a silicon-containing layer in contact with the first insulating film, a silicide-containing layer provided on the silicon-containing layer, and a first nitride film provided on a lower side of the silicide-containing layer.

4. The device according to claim 3, wherein a length from a lower end of the silicon-containing layer to a junction between the silicon-containing layer and the silicide-containing layer is longer than a length from the junction to an upper end of the silicide-containing layer.

5. The device according to claim 3, wherein the second insulating film includes a second nitride film in contact with the silicide-containing layer.

6. The device according to claim 3, wherein a width of the silicide-containing layer in the direction crossing the first direction is 5 nm (nanometers) or less.

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